

atoms, excited oxygen molecules, oxygen atoms, oxygen molecules, and ozone molecules. The radicals and excited species included in the plasma are supplied into a substrate processing region that is separated or isolated from the plasma generation region. Independently of the excited species and radicals, monosilane gas is also supplied into the substrate processing region, where a gas phase reaction between the oxygen gas and the monosilane gas occurs. The gas phase reaction produces precursors which are for silicon dioxide (SiO_2) and are for example SiH_x , SiH_xO_y , SiO_y and so on. The precursors are adhered to a substrate or a wafer arranged within the substrate processing region and are subjected to oxidation, thermal dissociation and so forth, so that the silicon dioxide film are formed on the substrate or the wafer. Silicon nitride (Si_3N_4) film and an amorphous silicon (a-Si) film can be formed in the way similar to the above-mentioned remote plasma CVD process.--

Please replace the paragraph beginning at page 3, line 18, with the following rewritten paragraph:

--The plate is arranged between the plasma generation region and the processing region and is formed with a plurality of perforated holes through which the radicals pass. The plate is designed such that aperture ratio of the perforated holes to the plate is not greater than five percent. Each perforated hole may have a diameter not larger than three millimeters.--

Please replace the paragraph bridging pages 12 and 13, beginning at page 12, line 28, with the following rewritten paragraph:

--Referring to Figs. 6 through 9, a remote plasma CVD apparatus according to another embodiment of the present invention comprises the similar structure of the remote plasma CVD apparatus depicted in Fig. 5 except for an injection mechanism of the silane gas. Instead of the